To all our customers

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Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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PF08122B

MOS FET Power Amplifier Module
for E-GSM and DCS1800 Dual Band Handy Phone

RENESAS

ADE-208-1400H (Z)

Rev.8
Jul. 2002

Application

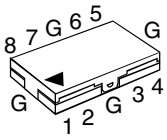
- Dual band amplifier for E-GSM (880 MHz to 915 MHz) and DCS1800 (1710 MHz to 1785 MHz).
- For 3.5 V & GPRS Class12 operation compatible

Features

- All in one including output matching circuit
- Simple external circuit
- Simple power control
- High gain 3stage amplifier : 0 dBm input Typ
- Lead less thin & Small package : 8 × 13.75 × 1.6 mm Typ
- High efficiency : 55% Typ at 35.0 dBm for E-GSM
  50% Typ at 32.5 dBm for DCS1800
- Lower consume current at low power
  100 mA Typ at 7 dBm for E-GSM
  60 mA Typ at 5 dBm for DCS1800

Pin Arrangement

• RF-K-8A



1: Pin $_{GSM}$
2: Vapc
3: Vdd1
4: Pout $_{GSM}$
5: Pout $_{DCS}$
6: Vdd2
7: Vctl
8: Pin $_{DCS}$
G: GND

Absolute Maximum Ratings

(Tc = 25°C)

Item	Symbol	Rating	Unit	Remark
Supply voltage	Vdd	7.0	V	at no-operation
		5.0	V	at operation (50 Ω load)
Supply current	Idd_{GSM}	3.5	A	
	Idd_{DCS}	2	A	
Vctl voltage	Vctl	4	V	
Vapc voltage	Vapc	4	V	
Input power	Pin	10	dBm	
Operating case temperature	Tc (op)	−25 to +90	°C	
Storage temperature	Tstg	−30 to +100	°C	
Output power	$Pout_{GSM}$	5	W	
	$Pout_{DCS}$	3	W	

Note: The maximum ratings shall be valid over both the E-GSM-band (880 to 915 MHz), and the DCS1800-band (1710 to 1785 MHz).

Electrical Characteristics for DC

(Tc = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Drain cutoff current	Ids	—	—	20	μA	Vdd = 4.7 V, Vapc = 0 V, Vctl = 0.2 V
Vapc control current	Iapc	—	—	2.0	mA	Vapc = 2.2 V
Vctl control current	Ictl	—	—	2	μA	Vctl = 3 V

Electrical Characteristics for GSM900 band

(Tc = 25°C)

Test conditions unless otherwise noted:
f = 880 to 915 MHz, Vdd1 = Vdd2 = 3.5 V, Pin = 0 dBm, Vctl = 2.0 V, Rg = Rl = 50 Ω, Tc = 25°C,
Pulse operation with pulse width 1154 μs and duty cycle 2:8 shall be used.

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	880	—	915	MHz	
Band select (GSM active)	Vctl	2.0	—	2.8	V	
Input power	Pin	–2	0	2	dBm	
Control voltage range	Vapc	0.2	—	2.2	V	
Supply voltage	Vdd	3.0	3.5	4.5	V	
Total efficiency	η_T	47	55	—	%	$P_{out\ GSM}$ = 35 dBm, Vapc = controlled
2nd harmonic distortion	2nd H.D.	—	–45	–35	dBc	
3rd harmonic distortion	3rd H.D.	—	–45	–35	dBc	
4th~8th harmonic distortion	4th~8th H.D.	—	—	–35	dBc	
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	Pout (1)	35.0	36.0	—	dBm	Vapc = 2.2 V
Output power (2)	Pout (2)	33.5	34.5	—	dBm	Vdd = 3.1 V, Vapc = 2.2 V, Tc = +85°C
Idd at Low power	—	—	100	300	mA	$P_{out\ GSM}$ = 7 dBm
Isolation	—	—	–50	–37	dBm	Vapc = 0.2 V
Isolation at DCS RF-output when GSM is active	—	—	–25	–18	dBm	$P_{out\ GSM}$ = 35 dBm, Measured at f = 1760 to 1830 MHz
Switching time	t_r, t_f	—	1	2	μs	$P_{out\ GSM}$ = 5 to 35 dBm
Stability	—	No parasitic oscillation			—	Vdd = 3.1 to 4.5 V, Pout ≤ 35 dBm, $V_{apc\ GSM}$ ≤ 2.2 V, Rg = 50 Ω, Tc = 25°C, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	—	No degradation			—	Vdd = 3.1 to 4.5 V, $P_{out\ GSM}$ ≤ 35 dBm, $V_{apc\ GSM}$ ≤ 2.2 V, Rg = 50 Ω, t = 20 sec., Tc = 25°C, Output VSWR = 10 : 1 All phases
Load VSWR tolerance at GPRS CLASS 12 operation	—	No degradation			—	Vdd = 3.1 to 4.2 V, $P_{out\ GSM}$ ≤ 35 dBm, $V_{apc\ GSM}$ ≤ 2.2 V, Rg = 50 Ω, t = 20 sec., Tc ≤ 90°C, Output VSWR = 10 : 1 All phases
Slope Pout/Vapc	—	—	160	200	dB/V	$P_{out\ GSM}$ = 5 to 35 dBm
AM output	—	—	15	30	%	$P_{out\ GSM}$ = 5 to 35 dBm, 4% AM modulation at input 50 kHz modulation frequency

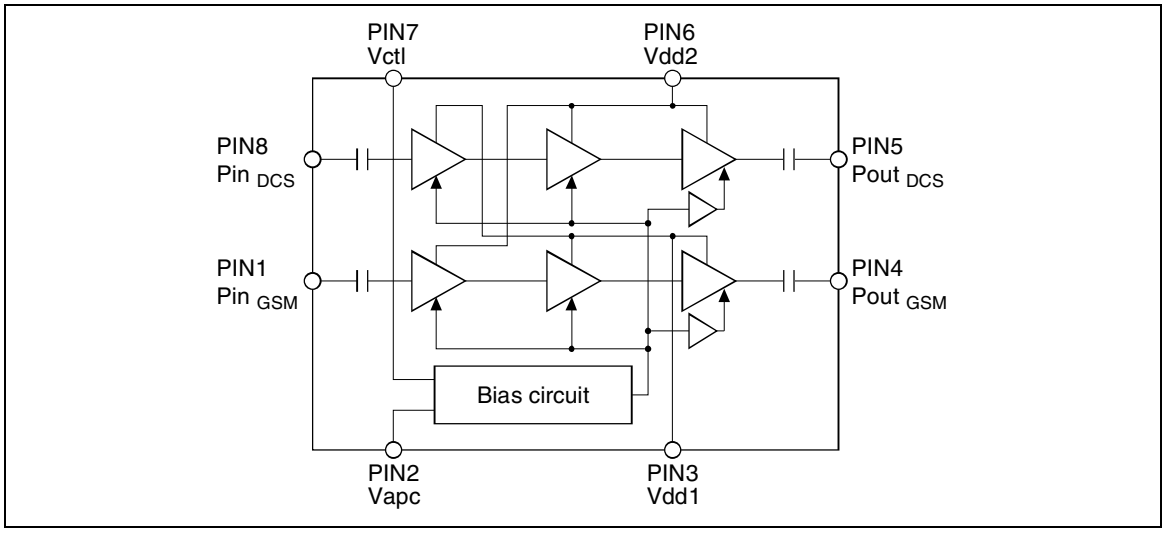
Electrical Characteristics for DCS1800 band

(Tc = 25°C)

Test conditions unless otherwise noted:
f = 1710 to 1785 MHz, Vdd1 = Vdd2 = 3.5 V, Pin = 0 dBm, Vctl = 0.2 V, Rg = Rl = 50 Ω, Tc = 25°C,
Pulse operation with pulse width 1154 µs and duty cycle 2:8 shall be used.

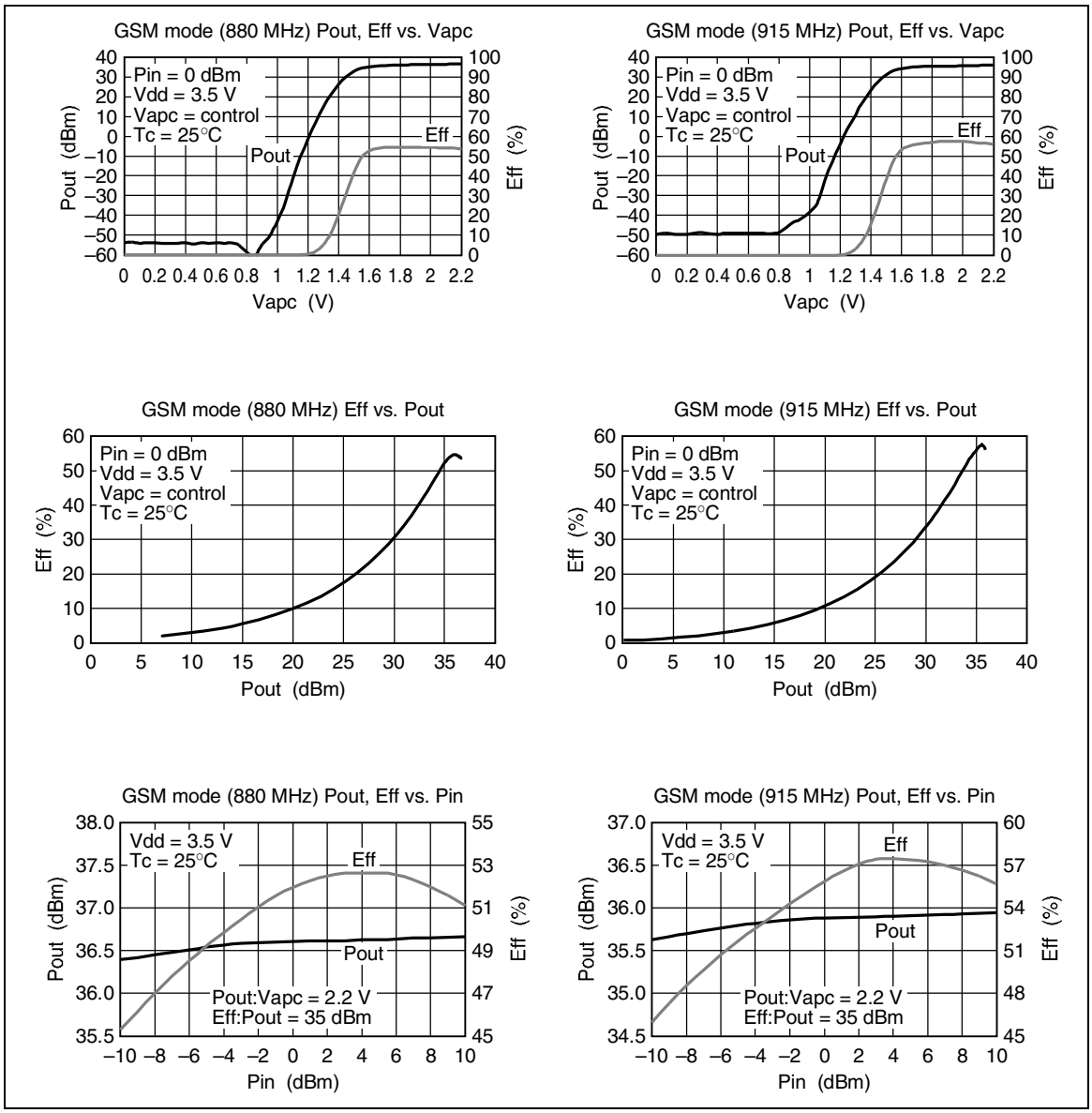
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	1710	—	1785	MHz	
Band select (DCS active)	Vctl	0	—	0.2	V	
Input power	Pin	–2	0	2	dBm	
Control voltage range	Vapc	0.2	—	2.2	V	
Supply voltage	Vdd	3.0	3.5	4.5	V	
Total efficiency	η_T	43	50	—	%	Pout $_{DCS}$ = 32.5 dBm, Vapc = controlled
2nd harmonic distortion	2nd H.D.	—	–45	–35	dBc	
3rd harmonic distortion	3rd H.D.	—	–45	–35	dBc	
4th~8th harmonic distortion	4th~8th H.D.	—	—	–35	dBc	
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	Pout (1)	32.5	33.5	—	dBm	Vapc = 2.2 V
Output power (2)	Pout (2)	31.0	32.0	—	dBm	Vdd = 3.1 V, Vapc = 2.2 V, Tc = +85°C,
Idd at Low power	—	—	60	150	mA	Pout $_{DCS}$ = 5 dBm
Isolation	—	—	–47	–37	dBm	Vapc = 0.2 V
Switching time	t_r, t_f	—	1	2	µs	Pout $_{DCS}$ = 0 to 32.5 dBm
Stability	—	No parasitic oscillation			—	Vdd = 3.1 to 4.5 V, Pout $_{DCS}$ ≤ 32.5 dBm, Vapc ≤ 2.2 V, Rg = 50 Ω, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	—	No degradation			—	Vdd = 3.1 to 4.5 V, Pout $_{DCS}$ ≤ 32.5 dBm, Vapc ≤ 2.2 V, Rg = 50 Ω, t = 20 sec., Tc = 25°C, Output VSWR = 10 : 1 All phases
Load VSWR tolerance at GPRS CLASS 12 operation	—	No degradation			—	Vdd = 3.1 to 4.2 V, Pout $_{DCS}$ ≤ 32.5 dBm, Vapc ≤ 2.2 V, Rg = 50 Ω, t = 20 sec., Tc ≤ 90°C, Output VSWR = 10 : 1 All phases
Slope Pout/Vapc	—	—	160	200	dB/V	Pout $_{DCS}$ = 0 to 32.5 dBm
AM output	—	—	15	30	%	Pout $_{DCS}$ = 0 to 32.5 dBm, 4% AM modulation at input 50 kHz modulation frequency

Circuit Diagram



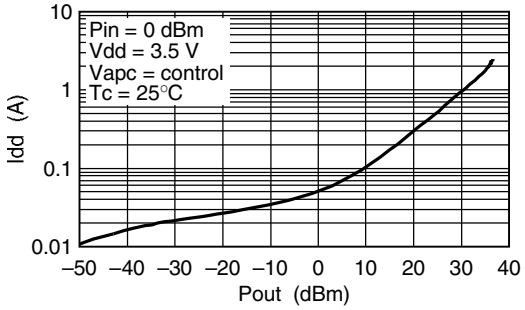
Characteristic Curves

GSM mode (880MHz to 915 MHz)

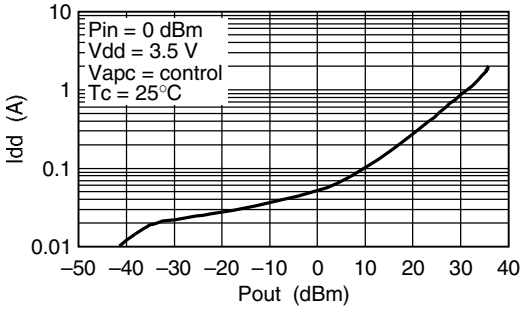


GSM mode (880MHz to 915 MHz) (cont)

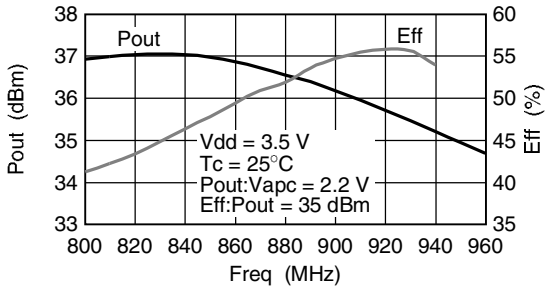
GSM mode (880 MHz) Idd vs. Pout



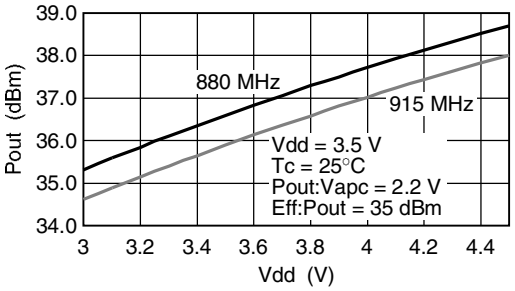
GSM mode (915 MHz) Idd vs. Pout



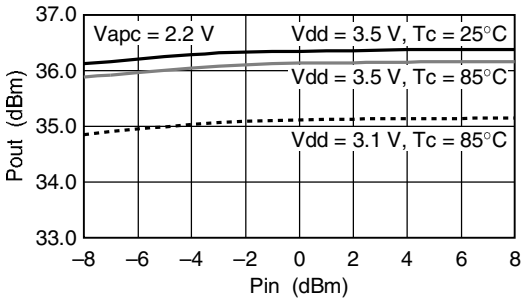
GSM mode Pout, Eff vs. Freq



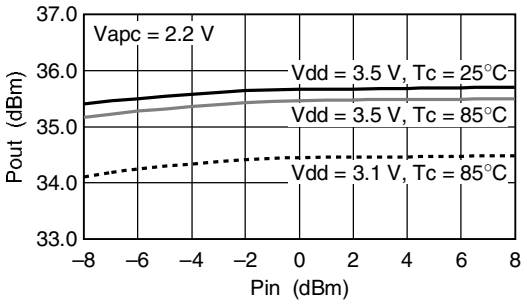
GSM mode Pout vs. Vdd



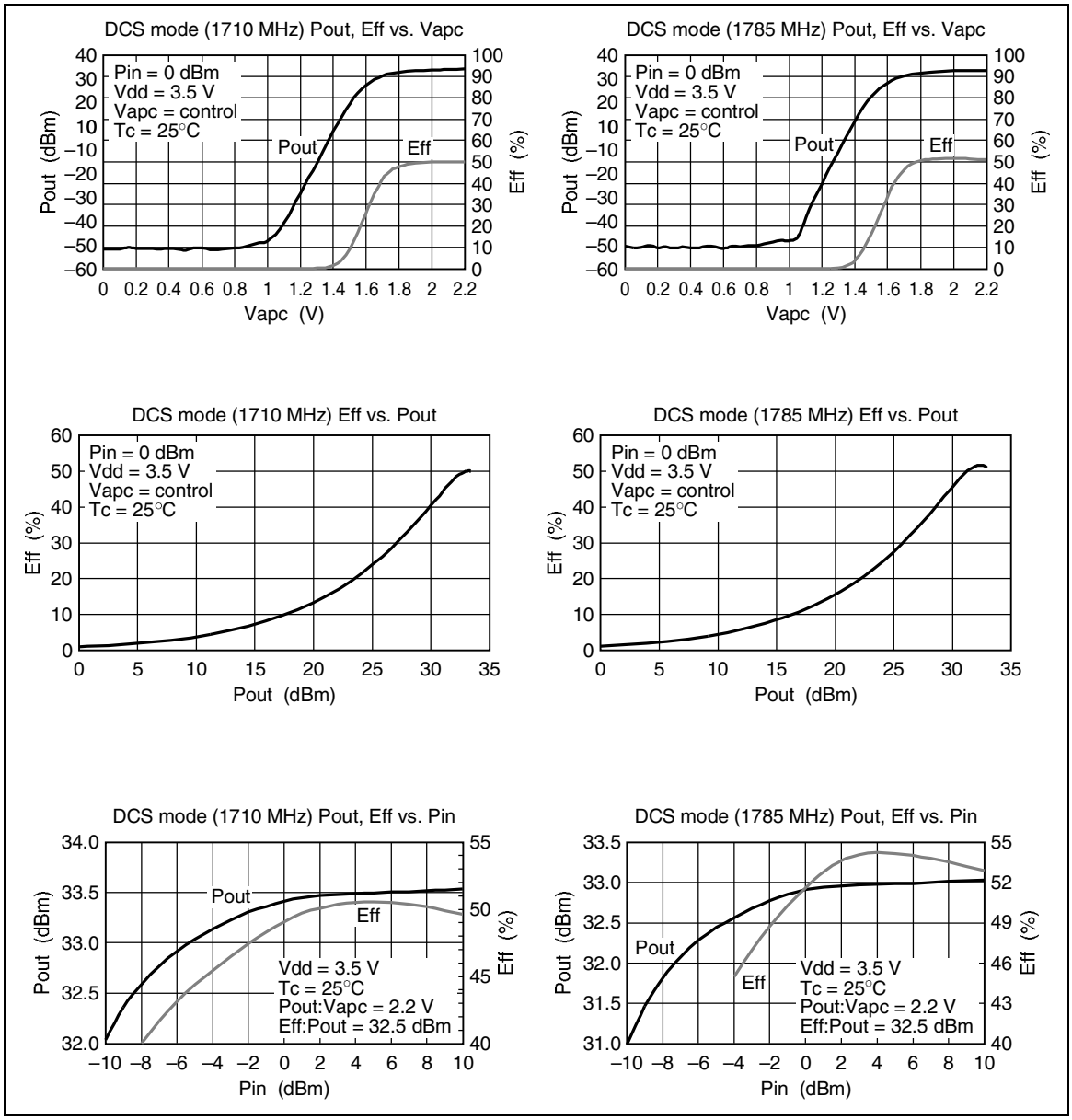
GSM mode (880 MHz) Pout vs. Pin (Temperature variation)



GSM mode (915 MHz) Pout vs. Pin (Temperature variation)

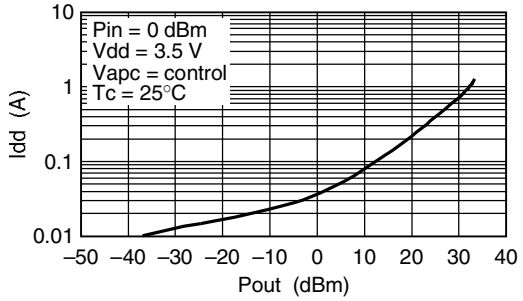


DCS mode (1710MHz to 1785 MHz)

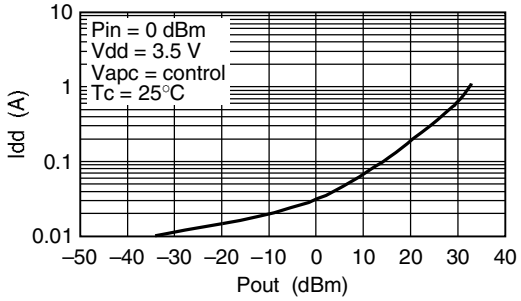


DCS mode (1710MHz to 1785 MHz) (cont)

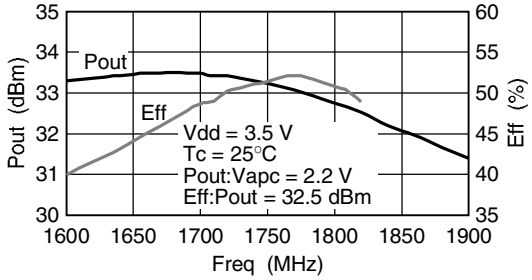
DCS mode (1710 MHz) Idd vs. Pout



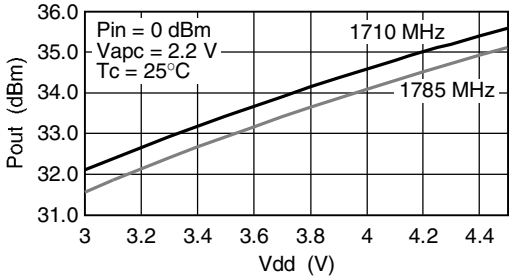
DCS mode (1785 MHz) Idd vs. Pout



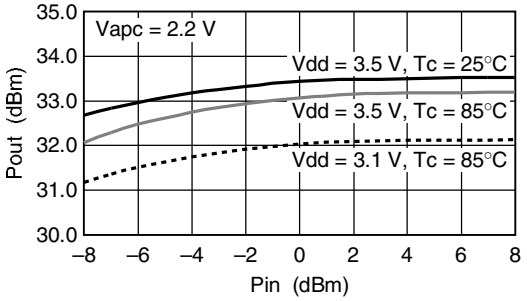
DCS mode Pout, Eff vs. Freq



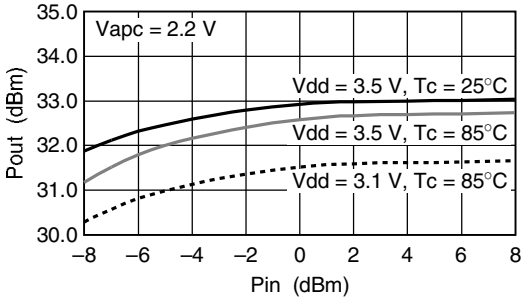
DCS mode Pout vs. Vdd



DCS mode (1710 MHz) Pout vs. Pin (Temperature variation)

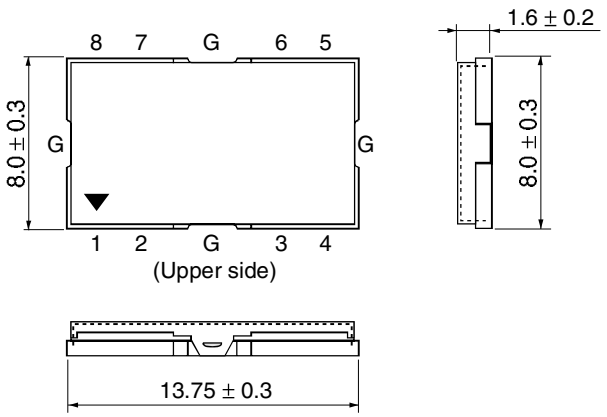


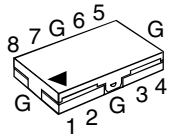
DCS mode (1785 MHz) Pout vs. Pin (Temperature variation)



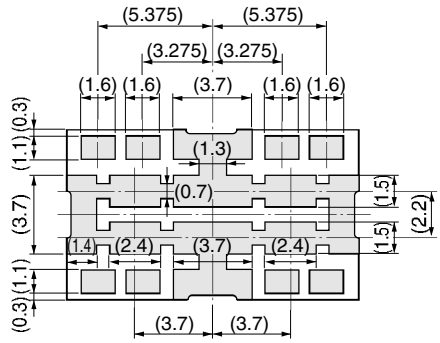
Package Dimensions

Unit: mm





1: Pin $_{GSM}$
2: Vapc
3: Vdd1
4: Pout $_{GSM}$
5: Pout $_{DCS}$
6: Vdd2
7: Vctl
8: Pin $_{DCS}$
G: GND



Remark:
Coplanarity of bottom side of terminals are less than 0 ± 0.1mm.

Hitachi Code	RF-K-8A
JEDEC	—
JEITA	—
Mass (reference value)	—

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